

Supplementary Materials

Tuning anatase-rutile phase transition temperature: TiO₂/SiO₂ nanoparticles applied in Dye-sensitized solar cells

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SEM

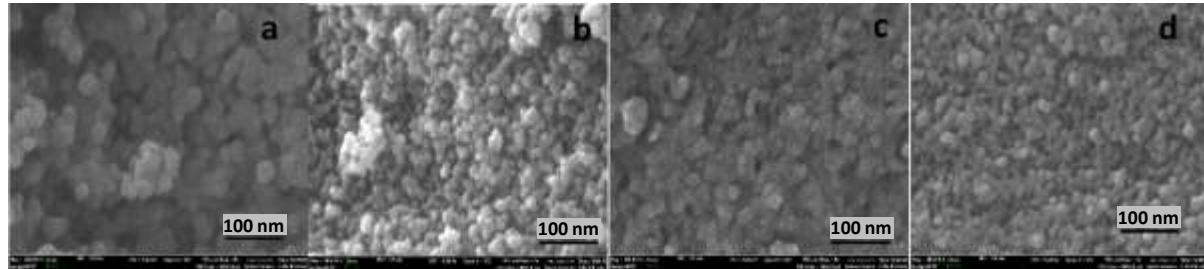


Figure S1: Scanning electron microscopy images of a) S0, b) S3, c) S5 and d) S10

Table S1: Carbon elemental analysis of the samples.

Sample	Molar % Ti	Molar % Si
S0	98 ± 3	2 ± 1
S3	97 ± 3	3 ± 1
S5	94 ± 3	6 ± 2
S10	90 ± 3	10 ± 2

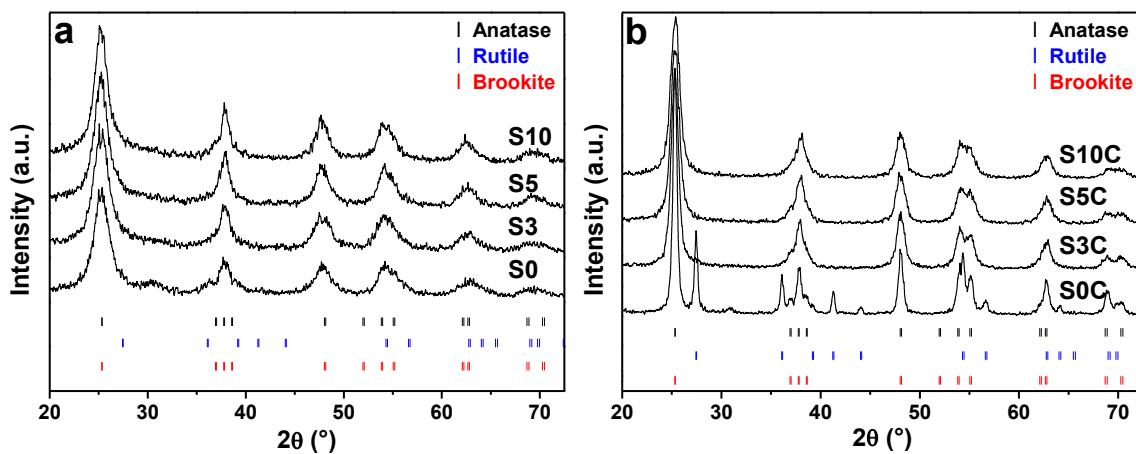
XRD

Figure S2: Diffraction patterns of the samples (a) before and (b) after thermal treatment at 500°C.

Raman spectroscopy

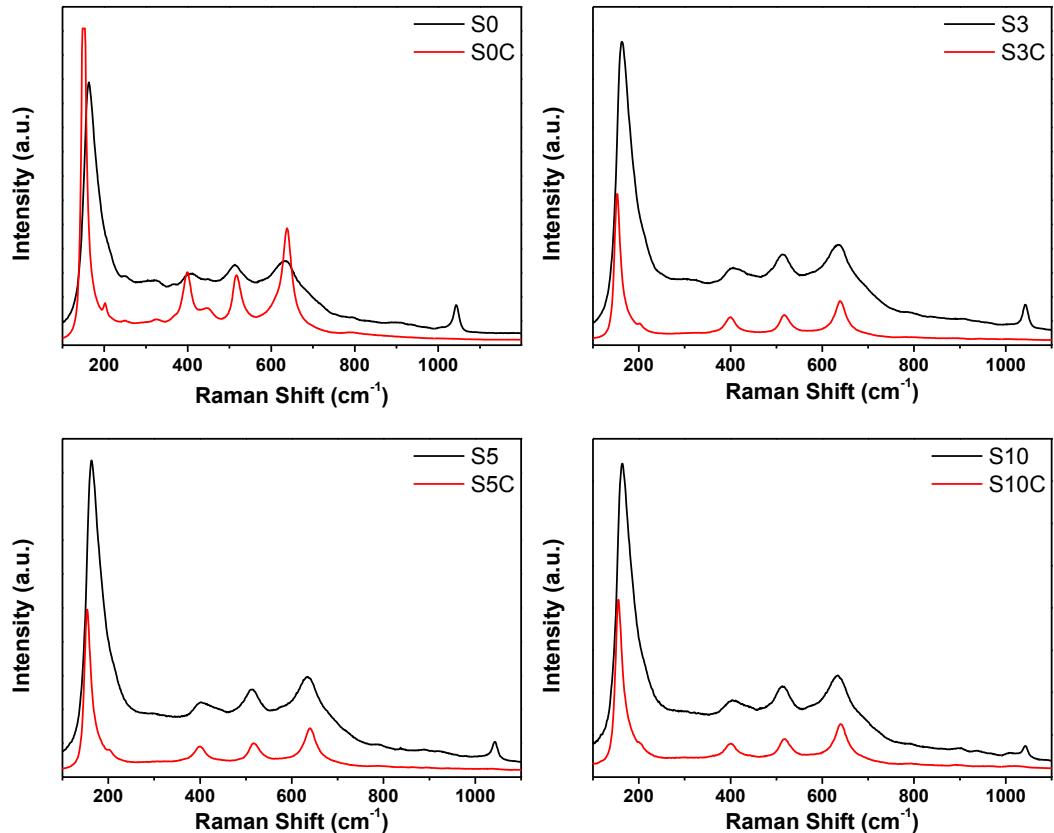


Figure S3: Raman Shift of S0, S3, S5 and S10 before and after thermal treatment.

UV-Visible

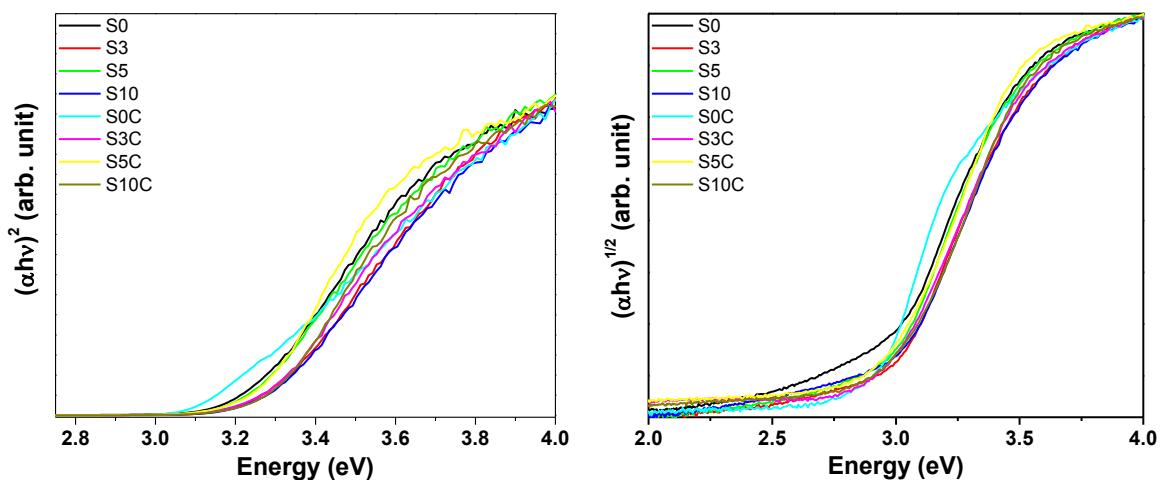


Figure S4: Direct (left) and indirect (right) Tauc Plot for S0, S3, S5 and S10.

Table S2: Direct and indirect band-gaps of the samples thermally treated at 500 °C.

Sample	Direct band-gap [eV]	Indirect band-gap [eV]
S0C	3.21	2.95
S3C	3.26	2.95
S5C	3.26	2.95
S10C	3.29	2.96

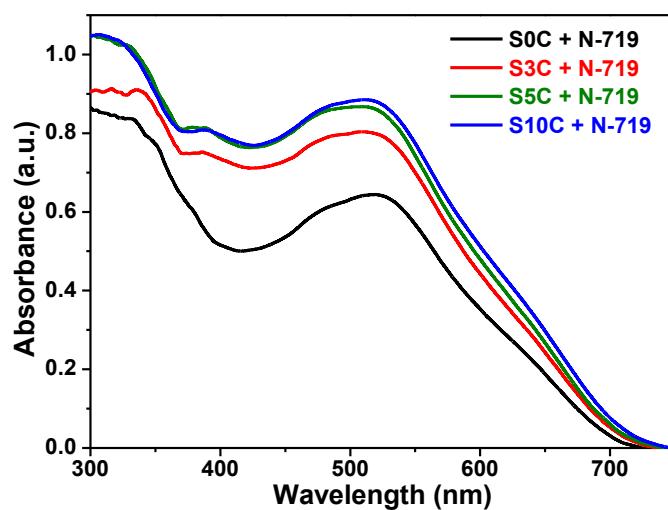


Figure S5: UV–Visible spectra of S0, S3, S5 and S10 thermally treated at 500 C and sensitized with N-719.